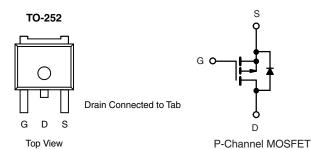


www.vishay.com

Vishay Siliconix

Automotive P-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	- 30				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.010				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.024				
I _D (A)	- 50				
Configuration	Single				



FEATURES

- TrenchFET® Power MOSFET
- · Package with Low Thermal Resistance
- AEC-Q101 Qualifiedd
- 100 % Rq and UIS Tested
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912



FREE

ORDERING INFORMATION			
Package	TO-252		
Lead (Pb)-free and Halogen-free	SQD45P03-12-GE3		

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	- 30	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C ^a	1	- 50		
	T _C = 125 °C	I _D	- 37		
Continuous Source Current (Diode Conduction) ^a		I _S	- 50	Α	
Pulsed Drain Current ^b		I _{DM}	- 200		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	- 31		
Single Pulse Avalanche Energy	L=U.I MH	E _{AS}	48	mJ	
Manianum Danum Diasimatianh	T _C = 25 °C	D	71	W	
Maximum Power Dissipation ^b	T _C = 125 °C	P_{D}	23	VV	
Operating Junction and Storage Temperature	e Range	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W	
Junction-to-Case (Drain)		R_{thJC}	2.1	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static	•	-			ı	ı	
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = - 250 μA		- 30	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = -250 \mu A$		- 2.0	- 2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = - 30 V	-	-	- 1	μА
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = - 30 V, T _J = 125 °C	-	-	- 50	
		$V_{GS} = 0 V$	V _{DS} = - 30 V, T _J = 175 °C	-	-	- 150	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = - 10 V	V _{DS} ≤ - 5 V	- 50	-	-	Α
		V _{GS} = - 10 V	I _D = - 15 A	-	0.008	0.010	
Drain-Source On-State Resistance ^a		V _{GS} = - 10 V	I _D = - 15 A, T _J = 125 °C	-	-	0.015	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = - 10 V	I _D = - 15 A, T _J = 175 °C	-	-	0.017	Ω
		V _{GS} = - 4.5 V	I _D = - 12 A	-	0.019	0.024	
Forward Transconductanceb	9 _{fs}	V _{DS} =	V _{DS} = - 15 V, I _D = - 17 A		34	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	2794	3495	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	V _{GS} = 0 V V _{DS} = - 15 V, f = 1 MHz		616	770	рF
Reverse Transfer Capacitance	C _{rss}			-	470	590	1
Total Gate Charge ^c	Qg			-	55.3	83	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = - 10 V	$V_{DS} = -15 \text{ V}, I_{D} = -45 \text{ A}$	-	7.3	-	nC
Gate-Drain Charge ^c	Q _{gd}	7			14	-	
Gate Resistance	R_g	f = 1 MHz		1.40	2.86	4.50	Ω
Turn-On Delay Time ^c	t _{d(on)}			-	11	16.5	
Rise Time ^c	t _r	V_{DD} = - 15 V, R_L = 0.33 Ω I_D \cong - 45 A, V_{GEN} = - 10 V, R_g = 1 Ω		-	11	16.5	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	29	43.5	
Fall Time ^c	t _f			-	19	28.5	
Source-Drain Diode Ratings and Characteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	- 200	Α
Forward Voltage	V_{SD}	$I_F = -40 \text{ A}, V_{GS} = 0$		_	- 0.9	- 1.5	V

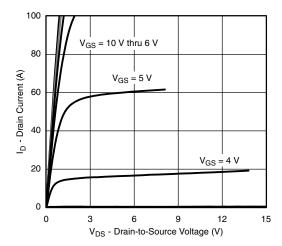
Notes

- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

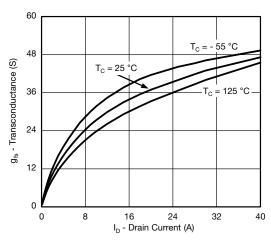
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



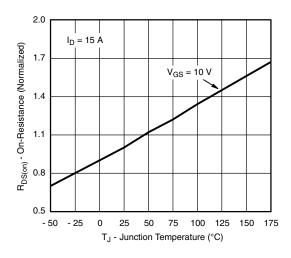
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



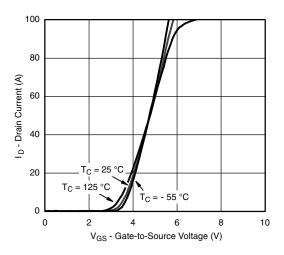
Output Characteristics



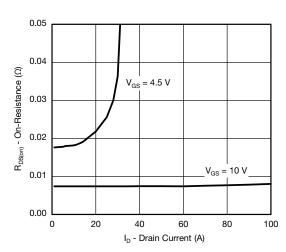
Transconductance



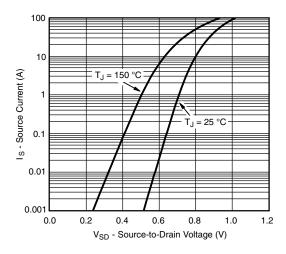
On-Resistance vs. Junction Temperature



Transfer Characteristics



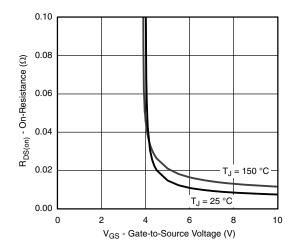
On-Resistance vs. Drain Current

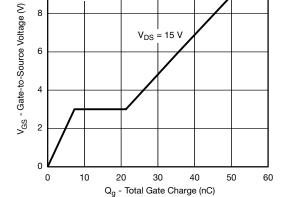


Source Drain Diode Forward Voltage



TYPICAL CHARACTERISTICS ($T_A = 25 \, ^{\circ}\text{C}$, unless otherwise noted)

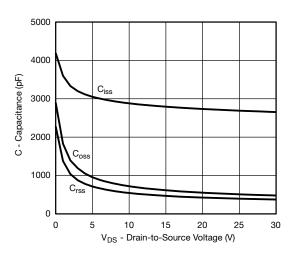




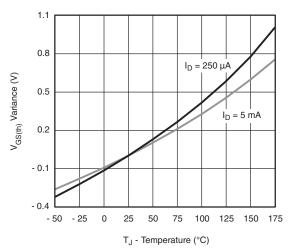
10

 $I_D = 45 A$

On-Resistance vs. Gate-to-Source Voltage

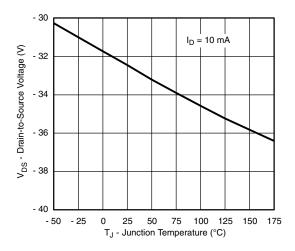


Gate Charge



Capacitance

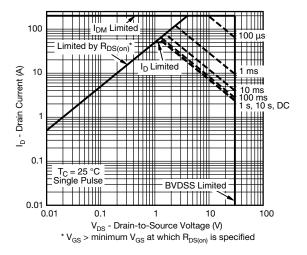
Threshold Voltage



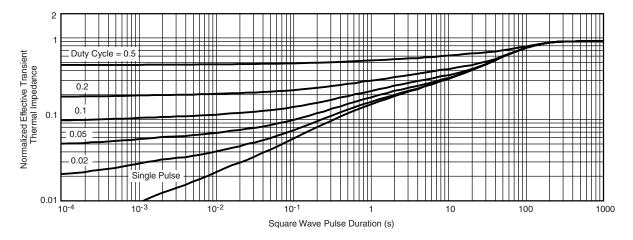
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



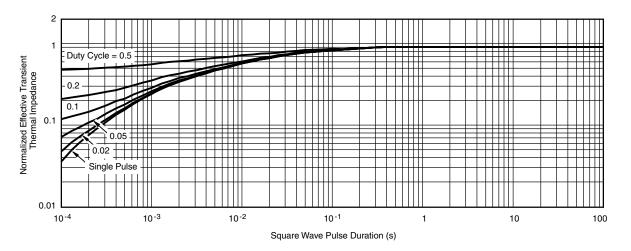
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

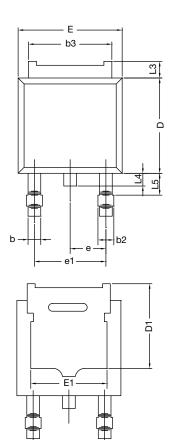
- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

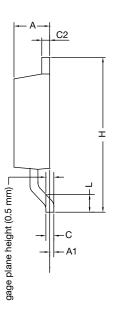
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg265549.





TO-252AA Case Outline



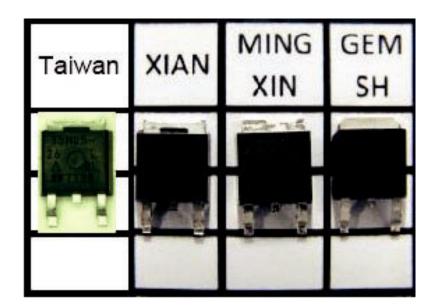


	MILLIN	METERS	INC	HES	
DIM.	MIN.	MAX.	MIN.	MAX.	
Α	2.18	2.38	0.086	0.094	
A1	-	0.127	-	0.005	
b	0.64	0.88	0.025	0.035	
b2	0.76	1.14	0.030	0.045	
b3	4.95	5.46	0.195	0.215	
С	0.46	0.61	0.018	0.024	
C2	0.46	0.89	0.018	0.035	
D	5.97	6.22	0.235	0.245	
D1	4.10	-	0.161	-	
Е	6.35	6.73	0.250	0.265	
E1	4.32	-	0.170	-	
Н	9.40	10.41	0.370	0.410	
е	2.28	BSC	0.090	BSC	
e1	4.56	BSC	0.180 BSC		
L	1.40	1.78	0.055	0.070	
L3	0.89	1.27	0.035	0.050	
L4	-	1.02	-	0.040	
L5	1.01	1.52	0.040	0.060	
ECN: T13-0359-Rev. O, 03-Jun-13					

DWG: 5347

Notes

- Dimension L3 is for reference only.
- Xi'an, Mingxin, and GEM SH actual photo.



Revision: 03-Jun-13 Document Number: 71197



RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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Revision: 02-Oct-12 Document Number: 91000